

Silicon PNP Power Transistors

2SA1718

DESCRIPTION

- With TO-220F package
- High DC current gain.
- Low collector saturation voltage.
- DARLINGTON

APPLICATIONS

- Ideal for motor drivers and solenoid drivers application

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

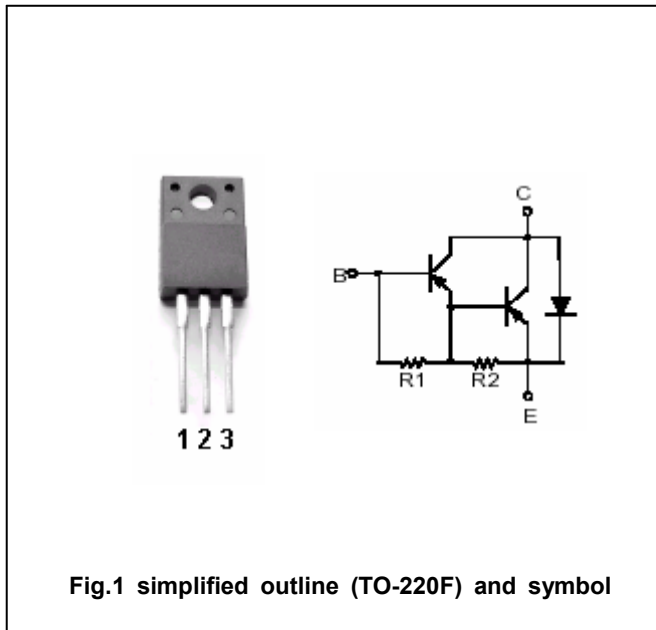


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-5	A
I _{CM}	Collector current-peak		-10	A
I _B	Base current		-0.5	A
P _C	Collector dissipation	T _C =25°C	20	W
		T _a =25°C	2.0	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-30mA; I _B =0	-100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-2mA			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A; I _B =-2mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-5.0	mA
h _{FE-1}	DC current gain	I _C =-2A; V _{CE} =-2V	2000		20000	
h _{FE-2}	DC current gain	I _C =-4A; V _{CE} =-2V	500			

◆ h_{FE} classifications

M	L	K
2000-5000	4000-10000	8000-20000

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PACKAGE OUTLINE

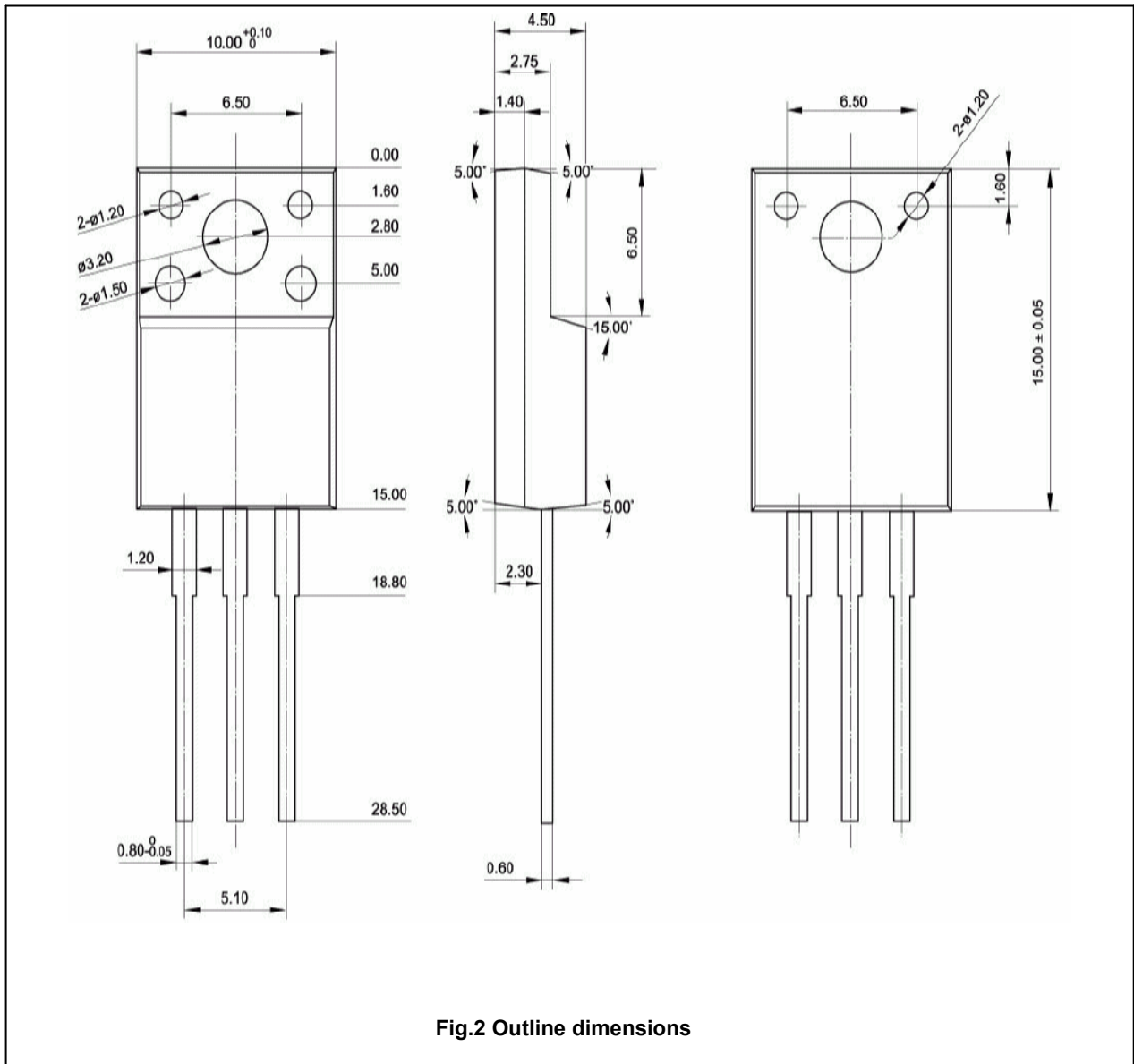


Fig.2 Outline dimensions